

Product Overview

AFGB30T65SQDN: IGBT 650V FS4 High speed version for OBC application in D2PAK

For complete documentation, see the data sheet.

Using the novel field stop 4th generation IGBT technology and AEC-Q101 Qualified. AFGB30T65SQDN offers the optimum performance with both low conduction loss and switching loss for a high efficiency operation in various applications.

Features

- AEC-Q101 Qualified
- $V_{CE(sat)} = 1.6\text{ V (typ.) @ } I_C = 30\text{ A}$
- Low V_F soft recovery co-packaged diode

Applications

- Automotive On Board Charger
- Automotive DC/DCC converter for HEV

Benefits

- For Automotive
- Low conduction loss
- Low noise and conduction loss

End Products

- EV/PHEV

Part Electrical Specifications

Product	Pricing (\$/Unit)	Compliance	Status	$V_{CE(s)}^{(BR)}$ Typ (V)	I_C Max (A)	$V_{CE(s)}$ Typ (V)	V_F Typ (V)	E_{off} Typ (mJ)	E_{on} Typ (mJ)	T_r Typ (ns)	I_r Typ (A)	Gate Charge Typ (nC)	Short Circuit Withstand (μ s)	E_{AS} Typ (mJ)	P_D Max (W)	Co-Packaged Diode	Package Type
AFGB30T65SQDN	2.2571	AEC Qualified PPAP Capable Pb-free	Active	650	30	1.6	1.5	0.16	0.786	131		56	-	-	220	Yes	D2PAK-3 / TO-263-2

For more information please contact your local sales support at www.onsemi.com.

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